

FIG. 1B

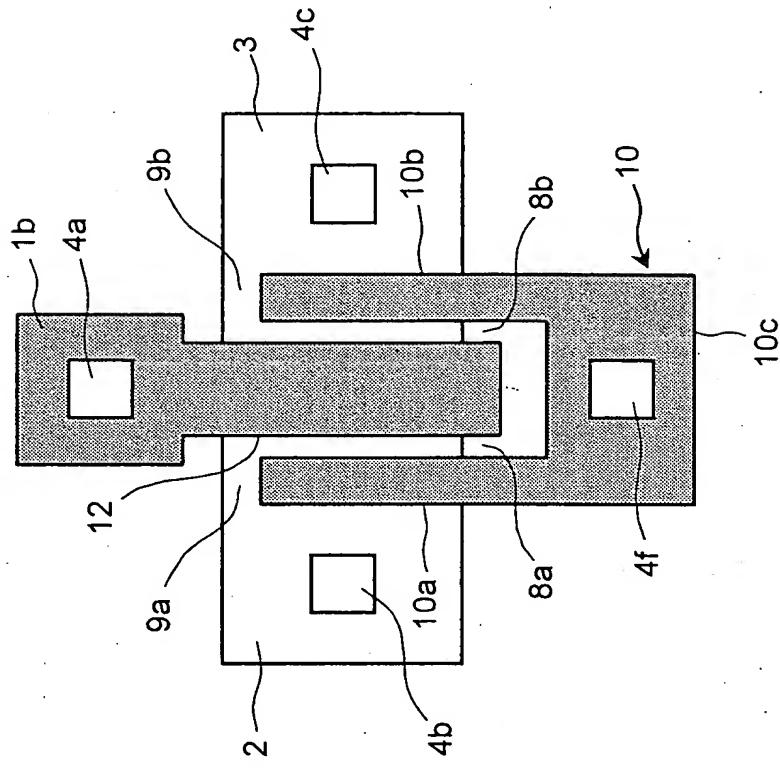
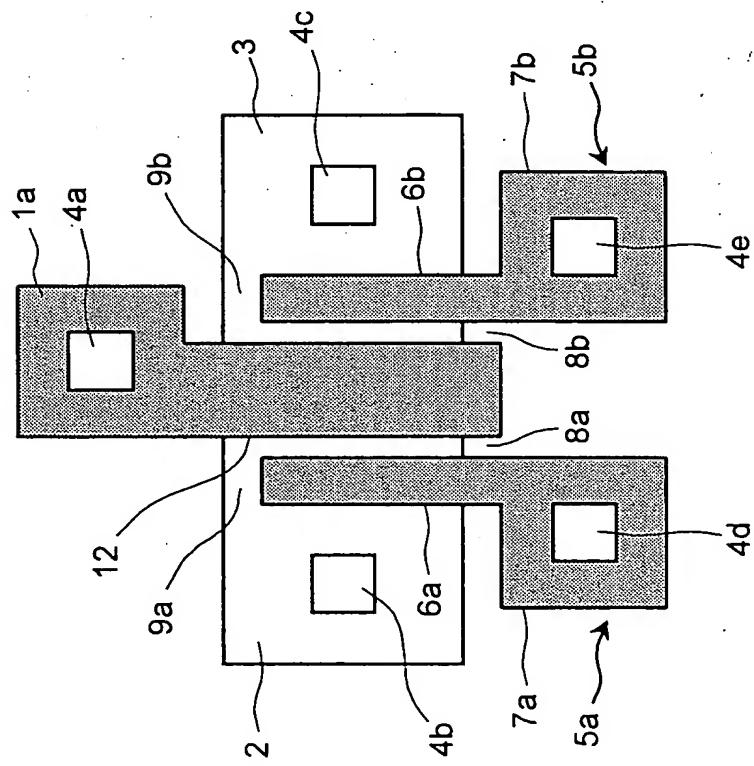


FIG. 1A



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FIG.2

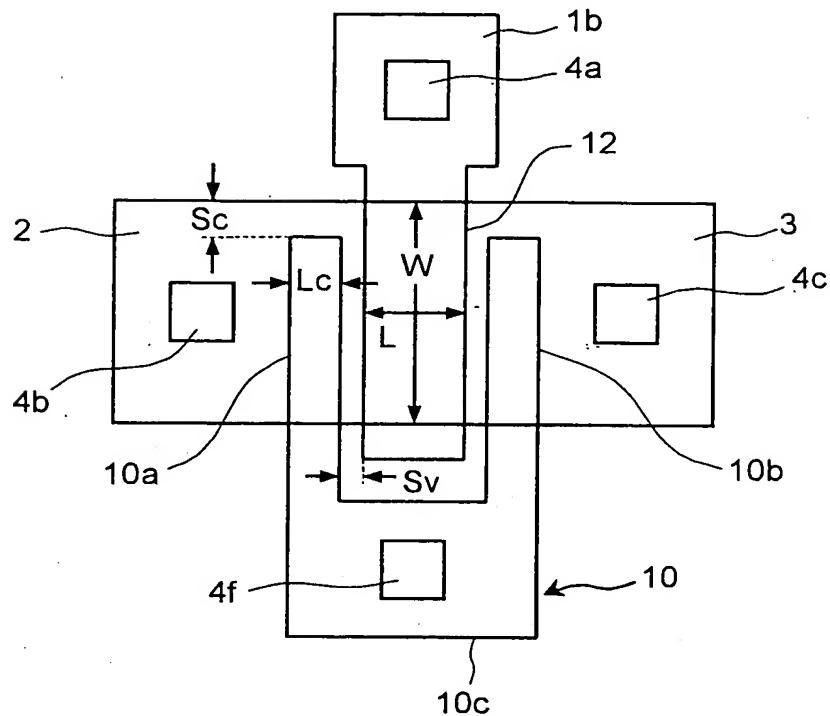


FIG.3

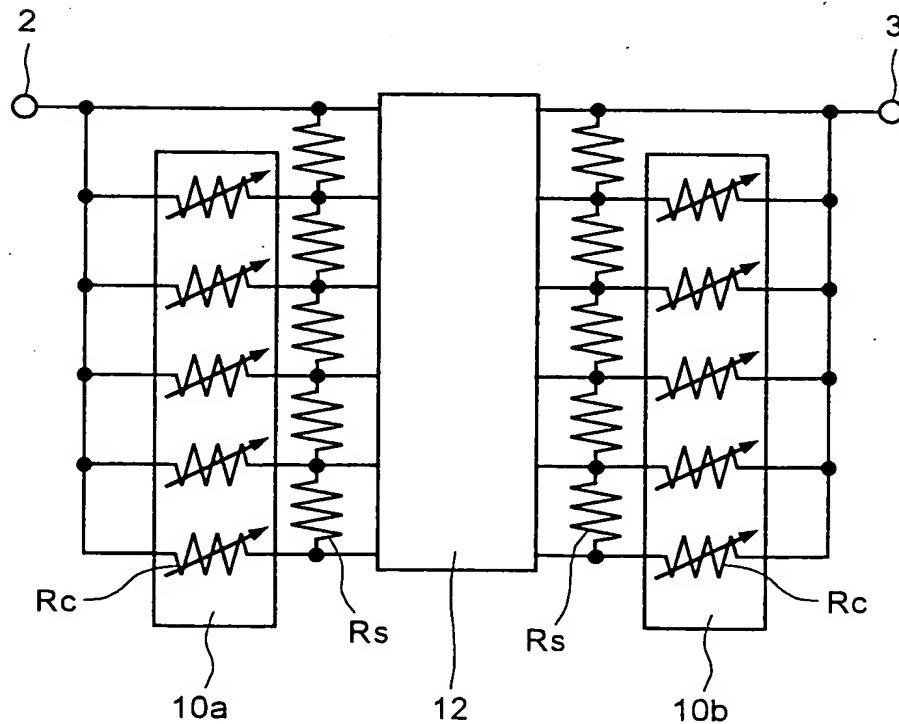
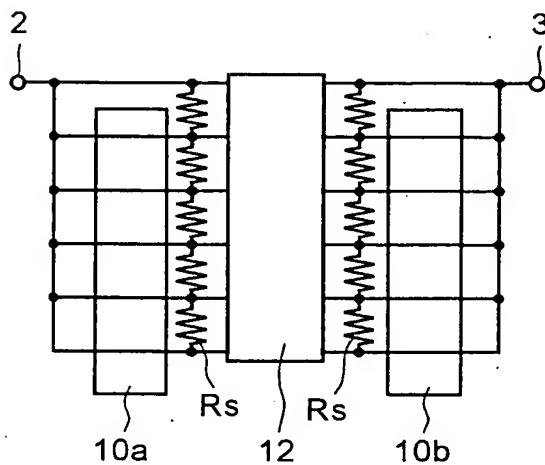
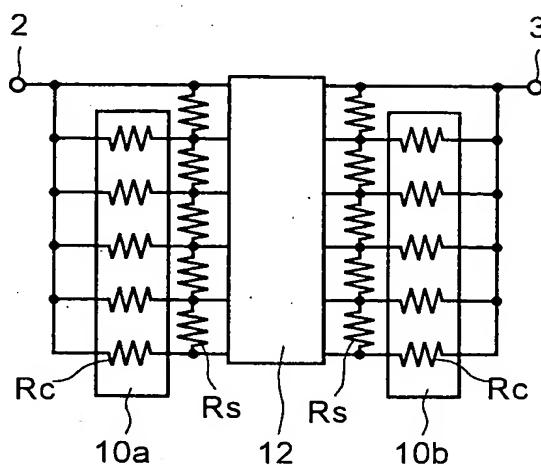


FIG.4A



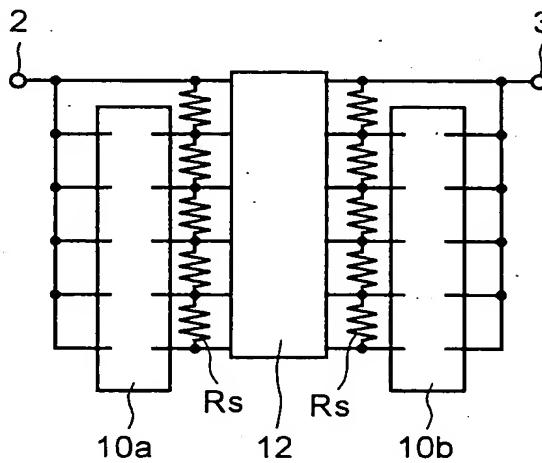
$G_c(\text{gate}) \ll G_c(\text{control gate})$

FIG.4B



$$G_c(\text{gate}) = G_c(\text{control gate})$$

FIG.4C



$G_c(\text{gate}) \gg G_c(\text{control gate})$

FIG.5C

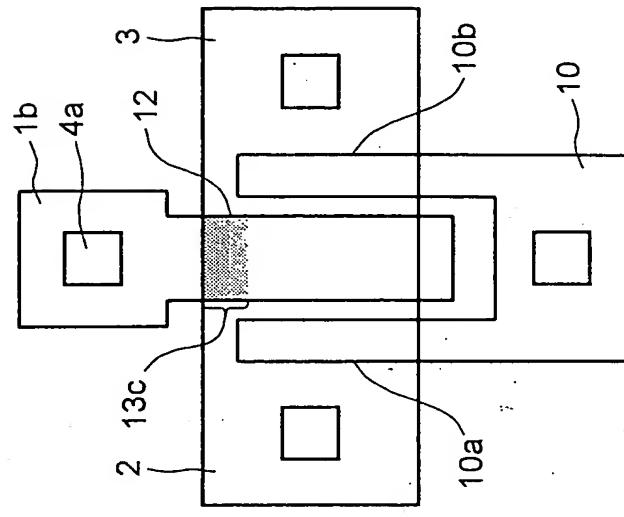


FIG.5B

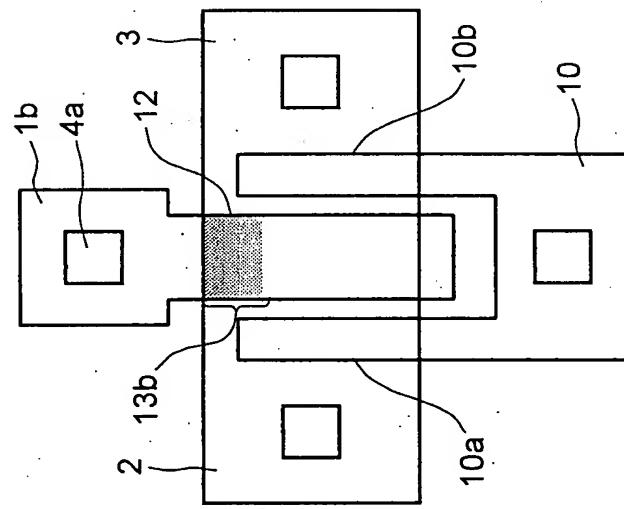
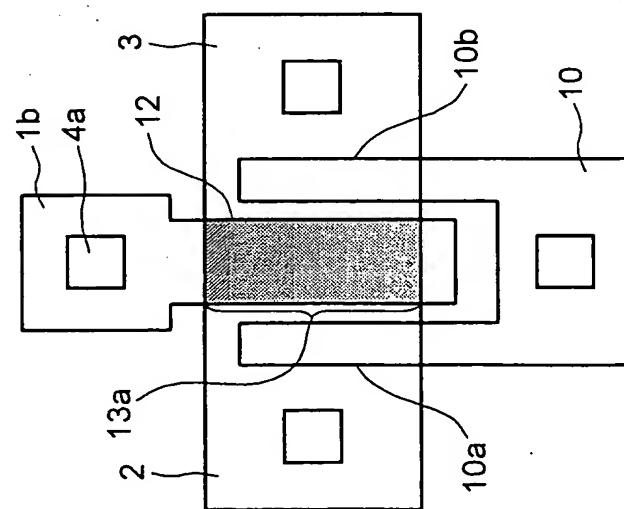


FIG.5A



G<sub>c</sub>(gate) << G<sub>c</sub>(control gate)

G<sub>c</sub>(gate) = G<sub>c</sub>(control gate)

G<sub>c</sub>(gate) >> G<sub>c</sub>(control gate)

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FIG.6A

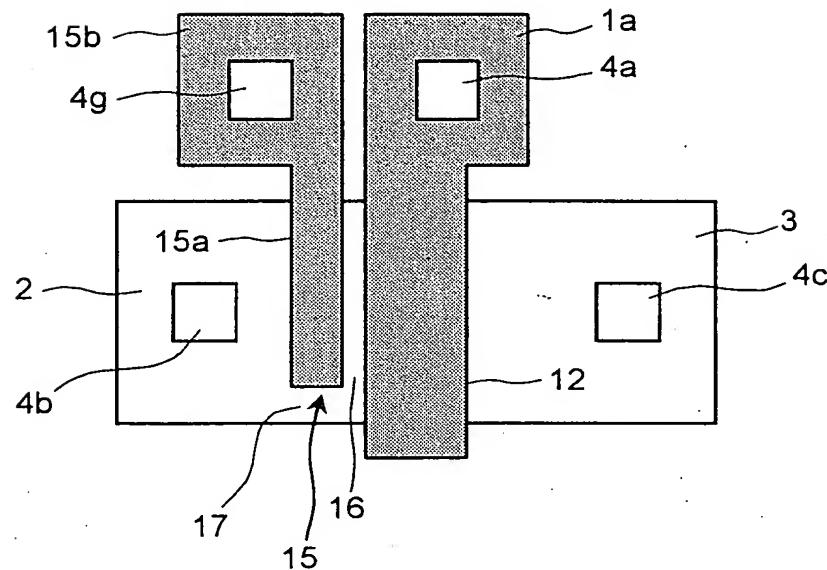
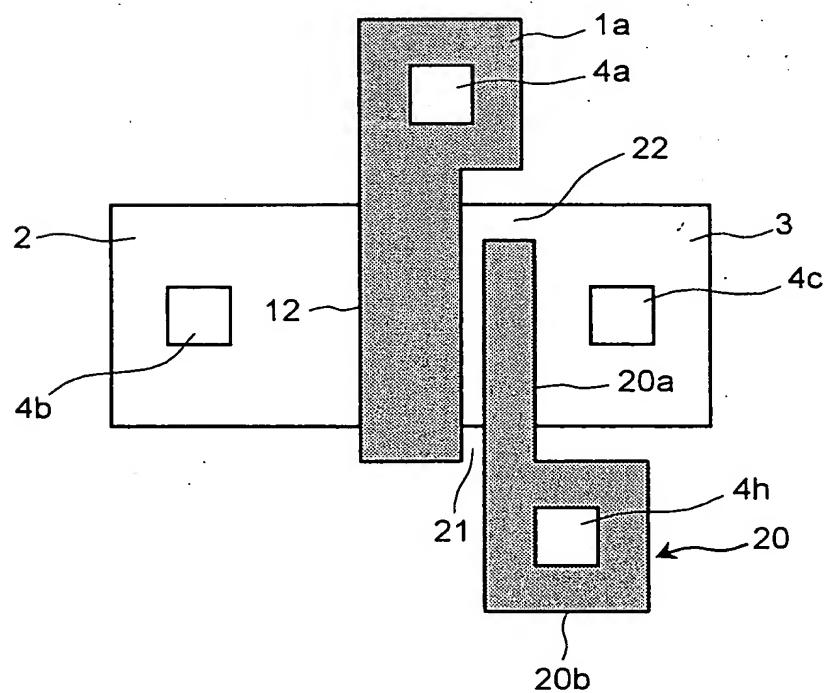


FIG.6B



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FIG.7

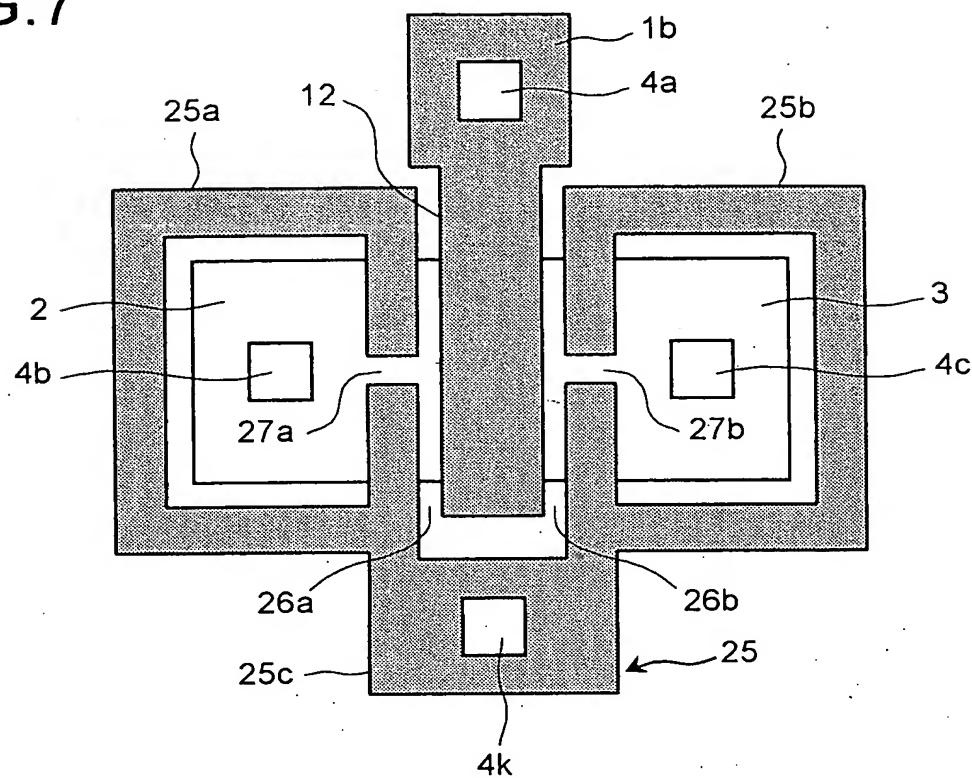
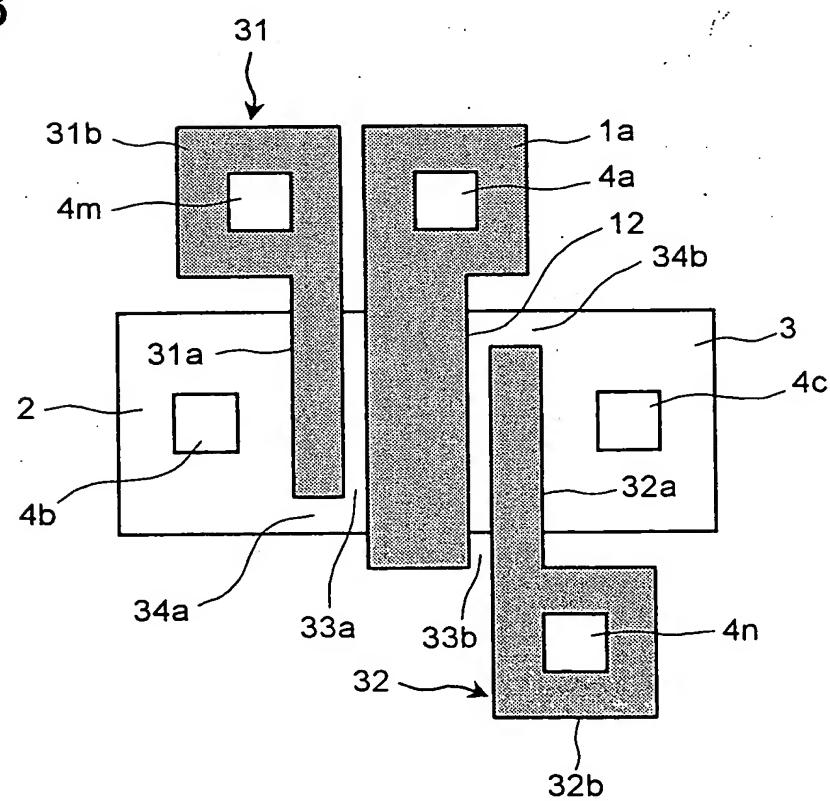


FIG.8



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FIG.9

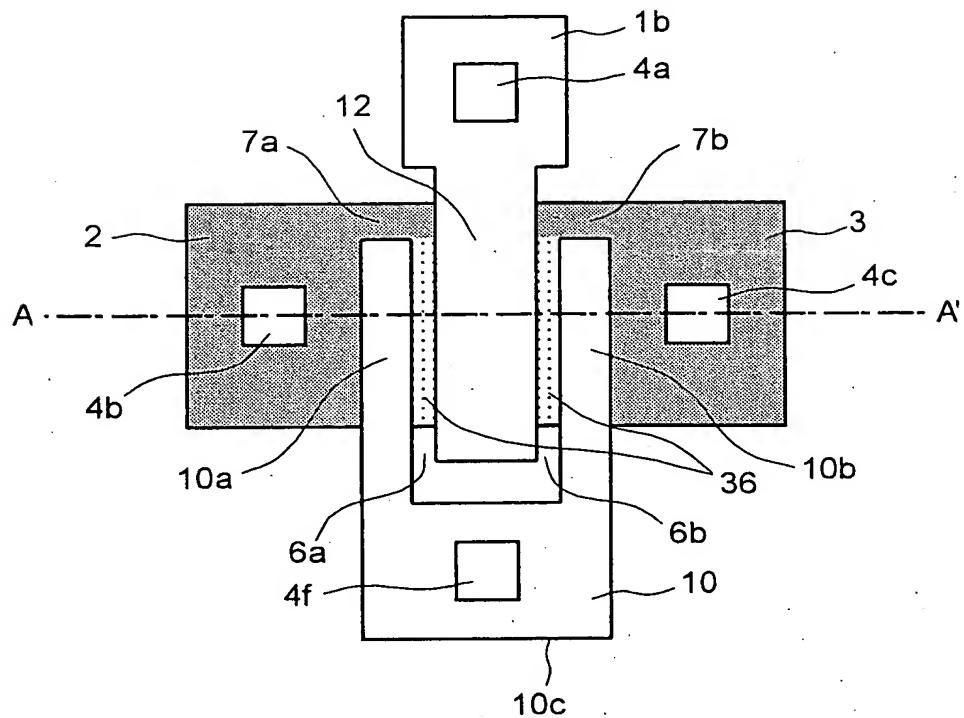
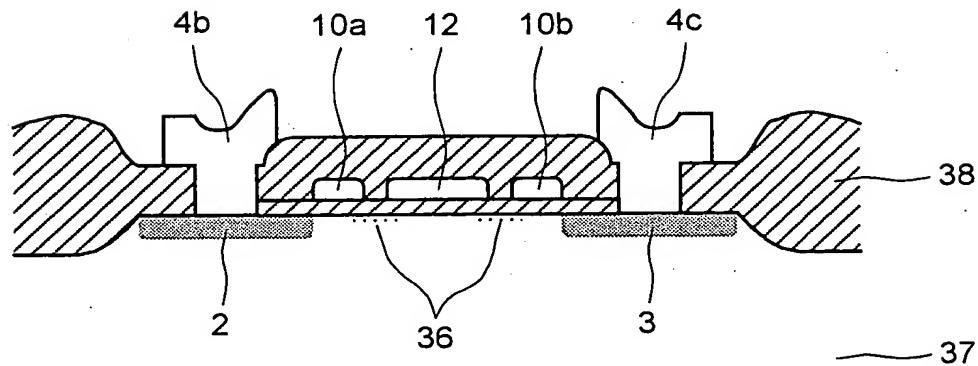


FIG.10



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FIG.11

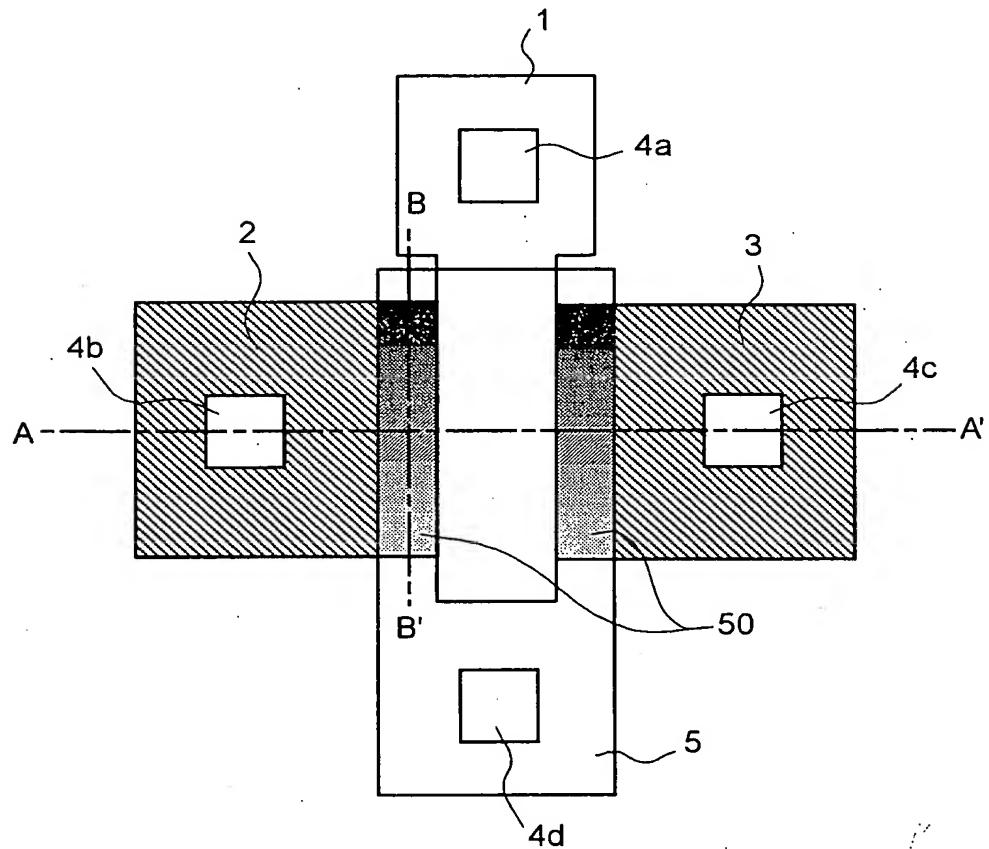
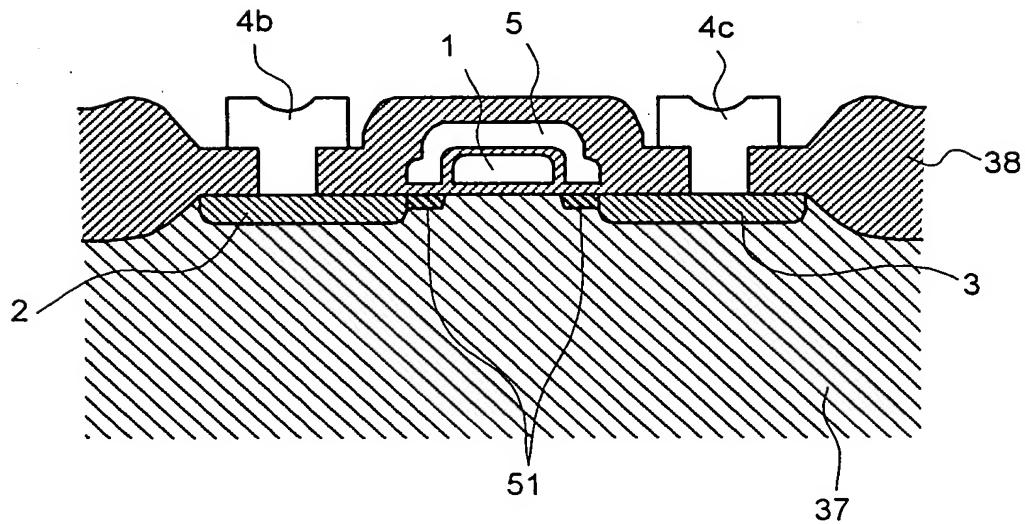


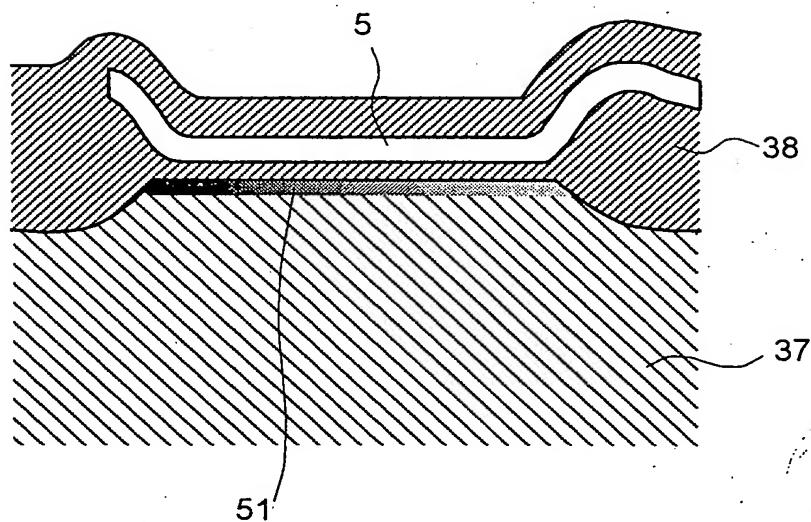
FIG.12



Title: METAL OXIDE SEMICONDUCTOR TRANSISTOR  
Inventors: Yutaka ARIMA  
Atty Docket No.: 402952  
Leydig, Voit & Mayer 202-737-6770

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FIG. 13



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FIG. 14

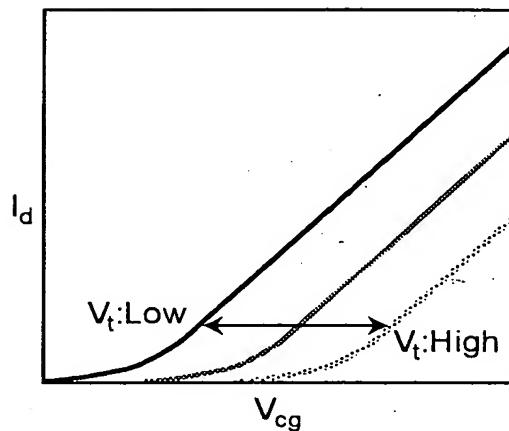
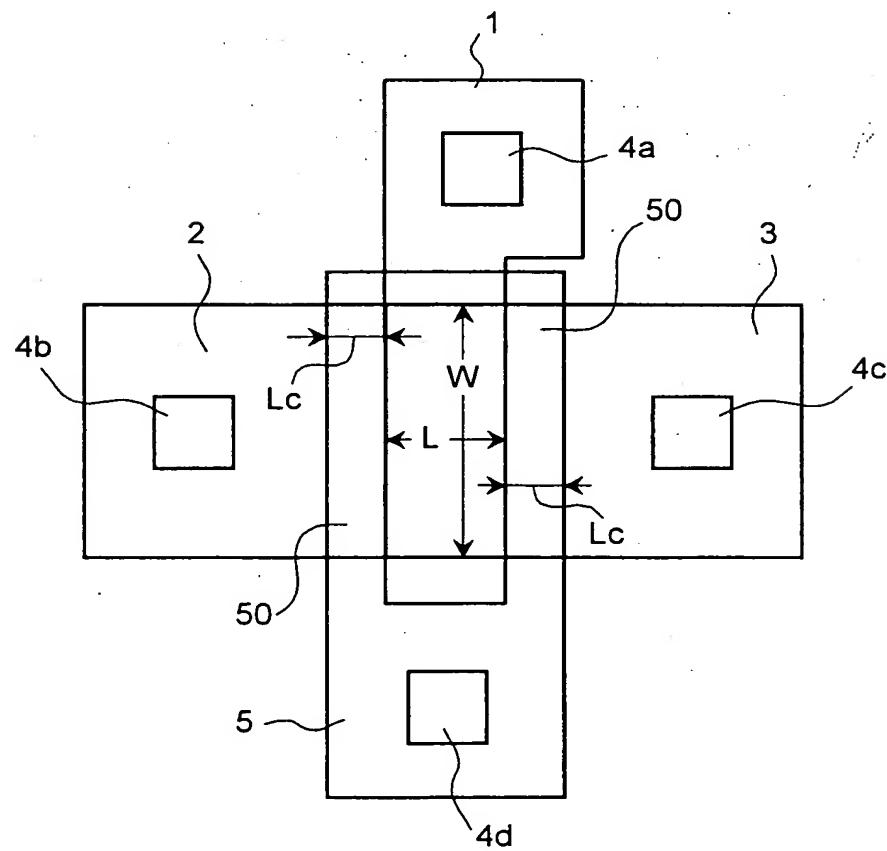
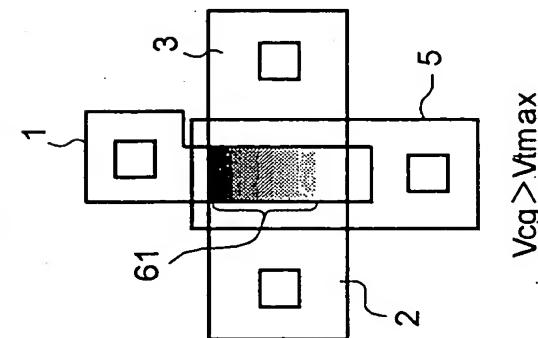


FIG. 15

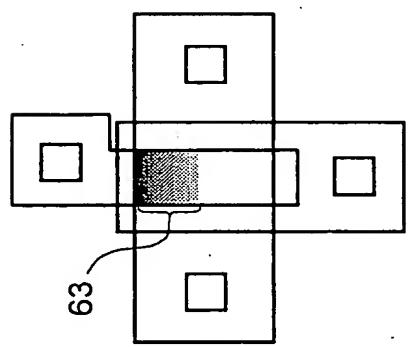


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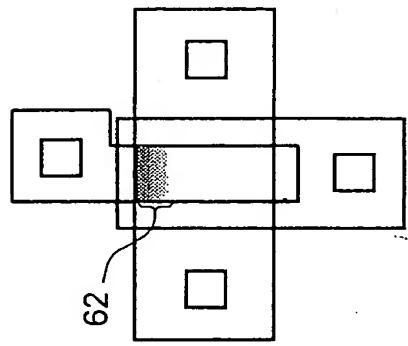
FIG.16A      FIG.16B      FIG.16C



$V_{cg} > V_{tmax}$



$V_{tmax} > V_{cg} > V_{tmiddle}$



$V_{tmiddle} > V_{cg} > V_{tmin}$

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FIG. 17

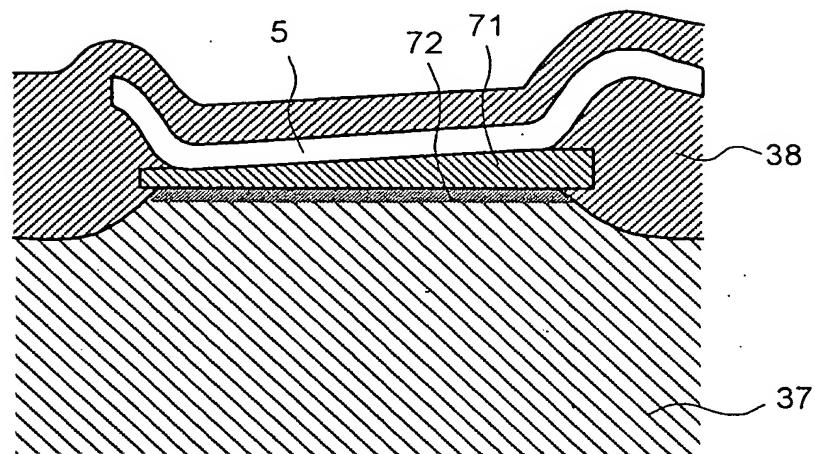
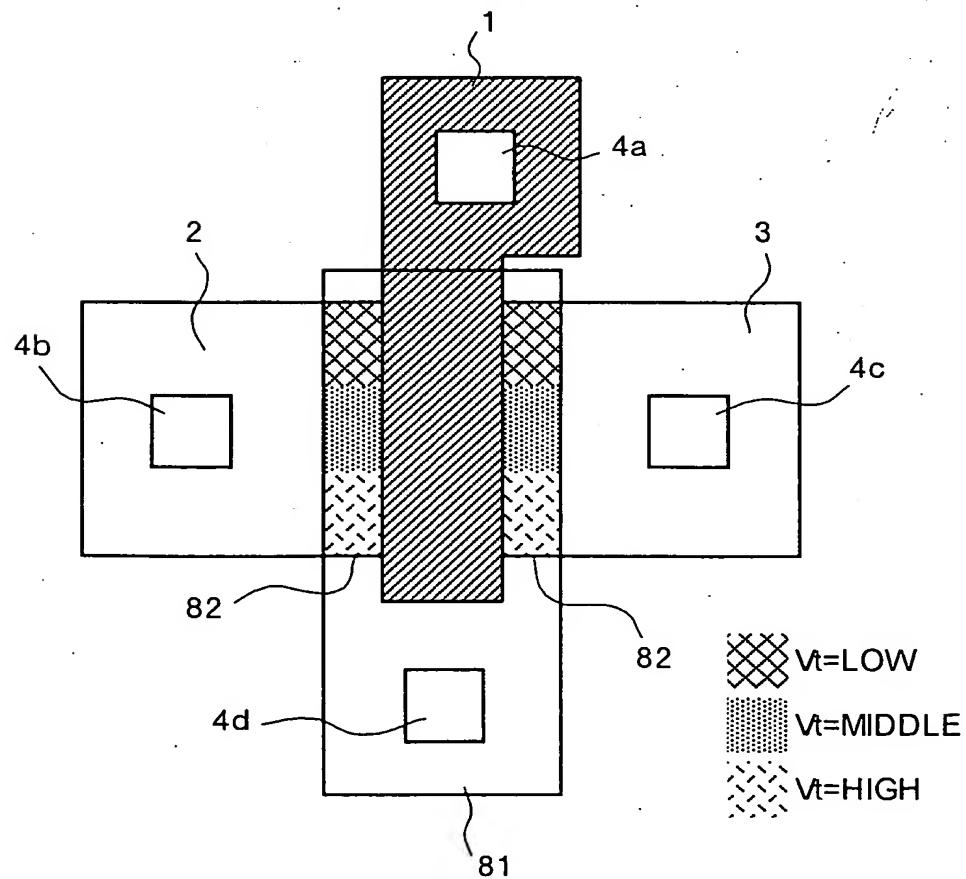


FIG. 18



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FIG.19

